

15. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming a semiconductor film through a sputtering method on an insulating surface;

adding a catalytic element into at least a portion of the semiconductor film, said catalytic element being capable of promoting crystallization; and

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

16. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming an amorphous semiconductor film comprising silicon and germanium through a sputtering method on an insulating surface;

adding a catalytic element into at least a portion of the semiconductor film, said catalytic element being capable of promoting crystallization;

crystallizing the semiconductor film to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

17. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming a base film on a plastic substrate;

forming a gate wiring on the base film;

forming a gate insulating film on the gate wiring;

forming a semiconductor film through a sputtering method on the gate insulating film;

crystallizing the semiconductor film to form a crystalline semiconductor film, wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

18. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming a gate wiring on an insulating surface;

forming a gate insulating film on the gate wiring;

forming a semiconductor film through a sputtering method on the gate insulating film;

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

19. (Amended) A method for manufacturing an electroluminescence display device comprising at least a thin film transistor, said method comprising the steps of:

forming a semiconductor film through a sputtering method on an insulating surface;

crystallizing the semiconductor film to form a crystalline semiconductor film;

forming a gate insulating film adjacent to the crystalline semiconductor film;

forming a gate electrode adjacent to the crystalline semiconductor film with the gate insulating film interposed therebetween;

introducing an impurity region into the crystalline semiconductor film to form at least a source region, a drain region and a channel region between the source and drain regions;

forming at least an interlayer insulating film over the thin film transistor;

forming a pixel electrode over the interlayer insulating film, said pixel electrode being electrically connected to the drain region of the thin film transistor;

forming an EL layer adjacent to the pixel electrode;

forming a cathode adjacent to the EL layer,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

Please add new claims 31-44.

--31. (New) A method according to claim 14, wherein the semiconductor device is selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device and an image sensor.

32. (New) A method according to claim 14, wherein the semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a navigation system for vehicles, a personal computer and a portable information terminal.

33. (New) A method according to claim 15, wherein the catalytic element includes at least an element selected from a group consisting of Ni, Fe, Co, Pt, Cu and Au.

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34. (New) A method according to claim 15, wherein the catalytic element includes at least an element selected from the group consisting of Ge and Pb.

35. (New) A method according to claim 15, wherein the semiconductor device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device and an image sensor.

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36. (New) A method according to claim 15, wherein the semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a navigation system for vehicles, a personal computer and a portable information terminal.

37. (New) A method according to claim 16, wherein the catalytic element includes at least an element selected from a group consisting of Ni, Fe, Co, Pt, Cu and Au.

38. (New) A method according to claim 16, wherein the catalytic element includes at least an element selected from the group consisting of Ge and Pb.

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39. (New) A method according to claim 16, wherein the semiconductor device is selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device and an image sensor.

40. (New) A method according to claim 16, wherein the semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a

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goggle display, a navigation system for vehicles, a personal computer and a portable information terminal.

41. (New) A method according to claim 17, wherein the semiconductor device is selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device and an image sensor.

42. (New) A method according to claim 17, wherein the semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a navigation system for vehicles, a personal computer and a portable information terminal.

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43. (New) A method according to claim 18, wherein the semiconductor device is selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device and an image sensor.

44. (New) A method according to claim 18, wherein the semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a navigation system for vehicles, a personal computer and a portable information terminal.--

REMARKS

Applicant would like to thank the Examiner for the consideration given the present application. The Office Action of April 17, 2001, has been received and its contents carefully noted. Applicant respectfully submits that this response is timely filed.